

# BSS138BKS

# 60 V, 320 mA dual N-channel Trench MOSFET Rev. 1 — 12 August 2011

**Product data sheet** 

#### **Product profile** 1.

## 1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1.5 kV
- AEC-Q101 qualified

## 1.3 Applications

- Relay driver
- High-speed line driver

- Low-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V
V <sub>GS</sub>	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	320	mA
Static characte	eristics (per transistor)						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V};$ $I_D = 320 \text{ mA}; T_j = 25 ^{\circ}\text{C}$		-	1	1.6	Ω

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



60 V, 320 mA dual N-channel Trench MOSFET

## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D4 D0
2	G1	gate TR1	<u>[6                                    </u>	D1 D2
3	D2	drain TR2		
4	S2	source TR2	0	$G1 \longrightarrow G2$
5	G2	gate TR2	□1 □2 □3	
6	D1	drain TR1	SOT363 (TSSOP6)	17
				S1 S2 017aaa256

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BSS138BKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

## 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BSS138BKS	LG%

<sup>[1] % =</sup> placeholder for manufacturing site code.

60 V, 320 mA dual N-channel Trench MOSFET

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	r					
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u>	-	320	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	<u>[1]</u>	-	210	mA
I <sub>DM</sub>	peak drain current	$T_{amb} = 25$ °C; single pulse; $t_p \le 10 \mu s$		-	1.2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	280	mW
			[1]	-	320	mW
		T <sub>sp</sub> = 25 °C		-	990	mW
Per device						
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	445	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	diode					
Is	source current	T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	320	mA
ESD maximu	m rating					
V <sub>ESD</sub>	electrostatic discharge voltage	HBM	[3]	-	1500	V

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[3]</sup> Measured between all pins.

#### 60 V, 320 mA dual N-channel Trench MOSFET

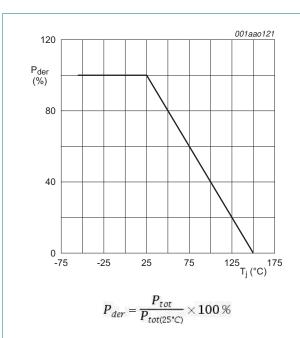


Fig 1. Normalized total power dissipation as a function of junction temperature

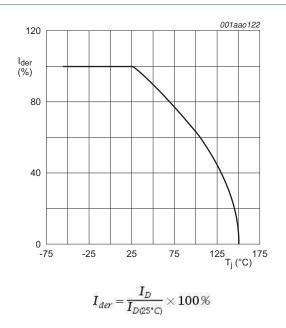
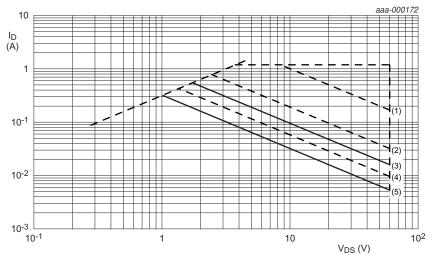


Fig 2. Normalized continuous drain current as a function of junction temperature



I<sub>DM</sub> is a single pulse

(1) 
$$t_p = 1 \text{ ms}$$

(2) 
$$t_p = 10 \text{ ms}$$

(3) DC; 
$$T_{sp} = 25 \, ^{\circ}C$$

$$(4) t_p = 100 ms$$

(5) DC; T<sub>amb</sub> = 25 °C; 1 cm<sup>2</sup> drain mounting pad

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 60 V, 320 mA dual N-channel Trench MOSFET

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	390	445	K/W
			[2] _	340	390	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	130	K/W
Per device						
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	300	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

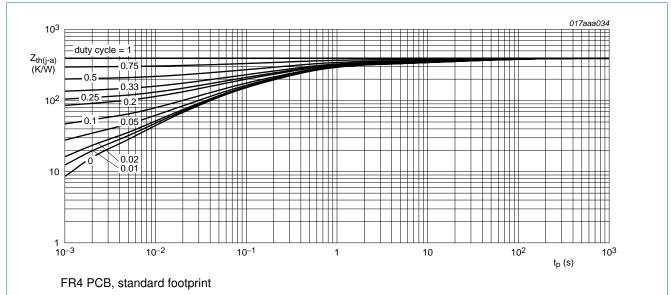


Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 320 mA dual N-channel Trench MOSFET

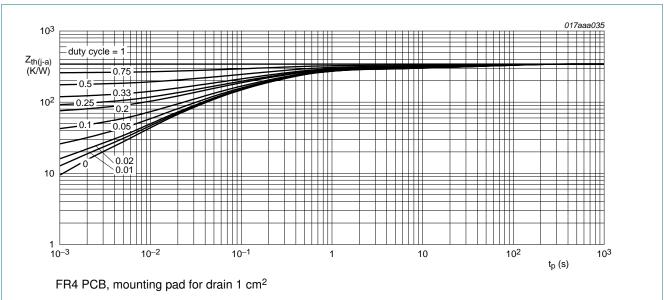


Fig 5. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 60 V, 320 mA dual N-channel Trench MOSFET

## 7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.48	1.1	1.6	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	10	μΑ
		$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 320 \text{ mA}; T_j = 25 \text{ °C}$	-	1	1.6	Ω
	resistance	$V_{GS} = 10 \text{ V}; I_D = 320 \text{ mA}; T_j = 150 \text{ °C}$	-	2	3.2	Ω
		$V_{GS} = 4.5 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	1.1	2.2	Ω
		$V_{GS} = 2.5 \text{ V}; I_D = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	1.4	6.5	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 200 \text{ mA}; T_j = 25 \text{ °C}$	-	700	-	mS
Dynamic	characteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 300 \text{ mA}; V_{GS} = 4.5 \text{ V};$	-	0.6	0.7	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	42	56	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	7	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 40 V; $R_L$ = 250 $\Omega$ ; $V_{GS}$ = 10 V;	-	5	10	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	38	76	ns
t <sub>f</sub>	fall time		-	20	-	ns
Source-di	rain diode (per transistor)					
$V_{SD}$	source-drain voltage	$I_S = 300 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	0.7	0.8	1.2	V

## 60 V, 320 mA dual N-channel Trench MOSFET

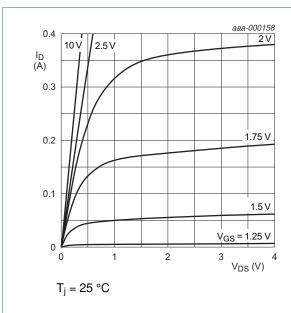
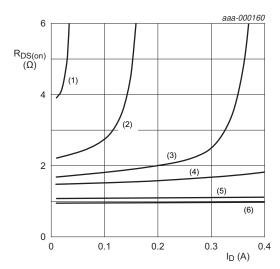


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \, ^{\circ}C$ 

(1)  $V_{GS} = 1.5 \text{ V}$ 

(2)  $V_{GS} = 1.75 \text{ V}$ 

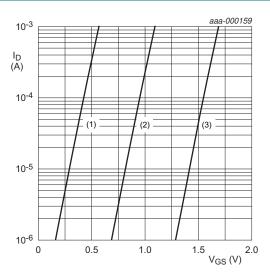
(3)  $V_{GS} = 2.0 \text{ V}$ 

(4)  $V_{GS} = 2.25 \text{ V}$ 

(5)  $V_{GS} = 4.5 \text{ V}$ 

(6)  $V_{GS} = 10 \text{ V}$ 

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



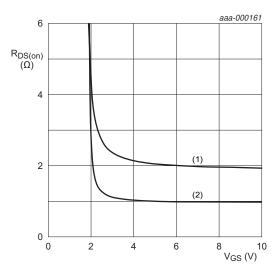
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$ 

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



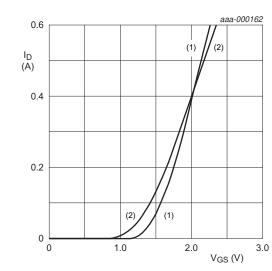
 $I_D = 300 \text{ mA}$ 

(1)  $T_j = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

## 60 V, 320 mA dual N-channel Trench MOSFET

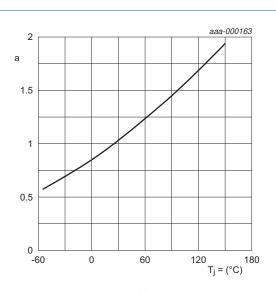


 $V_{DS} > I_D \times R_{DSon}$ 

(1) 
$$T_i = 25 \, ^{\circ}C$$

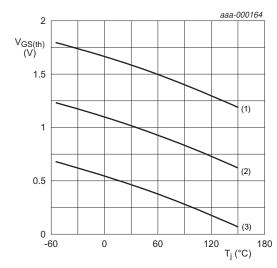
(2)  $T_i = 150 \, ^{\circ}\text{C}$ 

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



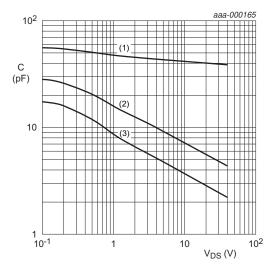
 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

(1) maximum values

(2) typical values

(3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$ 

(1) C<sub>iss</sub>

(2) C<sub>oss</sub>

(3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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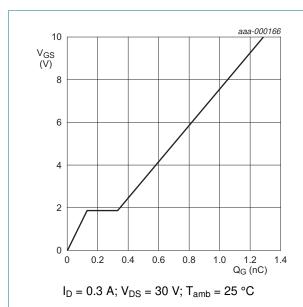


Fig 14. Gate-source voltage as a function of gate charge; typical values

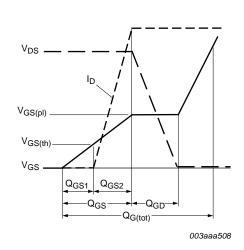
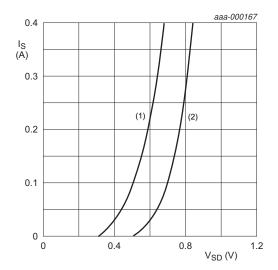


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

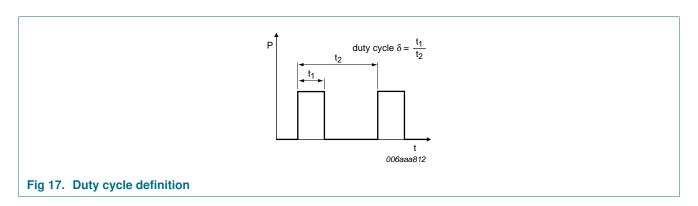
(1)  $T_j = 150 \, ^{\circ}C$ 

(2)  $T_j = 25 \, {}^{\circ}\text{C}$ 

Fig 16. Source current as a function of source-drain voltage; typical values

60 V, 320 mA dual N-channel Trench MOSFET

## 8. Test information



## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## Package outline

#### Plastic surface-mounted package; 6 leads **SOT363** Α X = v M A ⊕ w M B е detail X DIMENSIONS (mm are the original dimensions) Α1 UNIT Α D Ε С Q v е HΕ Lp w у max 0.30 0.25 1.35 0.45 0.25 1.1 2.2 2.2 0.65 0.1 1.8 2.0 0.20 0.10 8.0 1.15 0.15 0.15 **REFERENCES EUROPEAN** OUTLINE ISSUE DATE VERSION **PROJECTION** JEDEC IEC **JEITA** 04-11-08 SOT363 SC-88

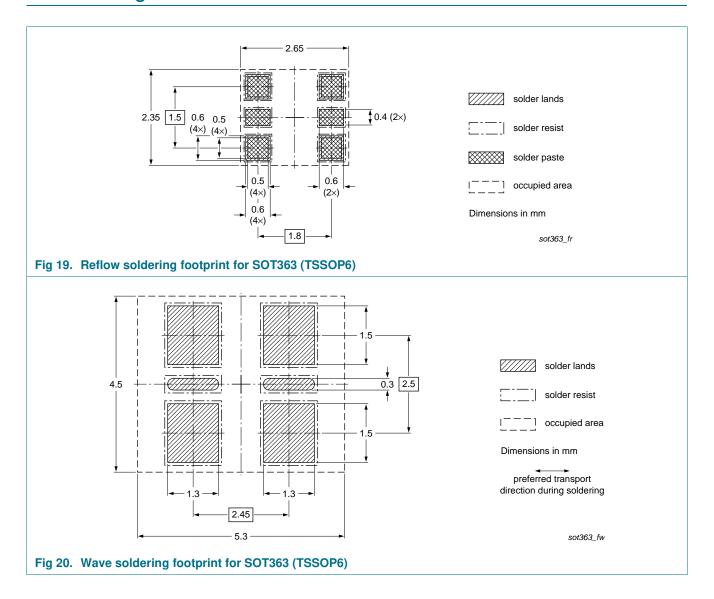
Fig 18. Package outline SOT363 (TSSOP6)

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06-03-16

## 60 V, 320 mA dual N-channel Trench MOSFET

## 10. Soldering



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# 11. Revision history

## Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BSS138BKS v.1	20110812	Product data sheet	-	-

#### 60 V, 320 mA dual N-channel Trench MOSFET

## 12. Legal information

#### 12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
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## 60 V, 320 mA dual N-channel Trench MOSFET

## 14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Marking
5	Limiting values
6	Thermal characteristics5
7	Characteristics
8	Test information11
8.1	Quality information
9	Package outline12
10	Soldering13
11	Revision history14
12	Legal information15
12.1	Data sheet status
12.2	Definitions15
12.3	Disclaimers
12.4	Trademarks16
13	Contact information